DSC018N10N

100V/1.5mΩ/240A N-MOSFET

Features

- Low on resistance
- Low reverse transfer capacitances
- 100% single pulse avalanche energy test
- 100% ΔVDS test
- Pb-Free plating / Halogen-Free / RoHS compliant

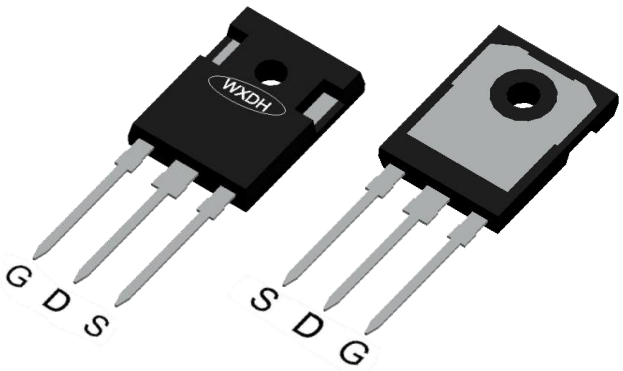
Key Parameters

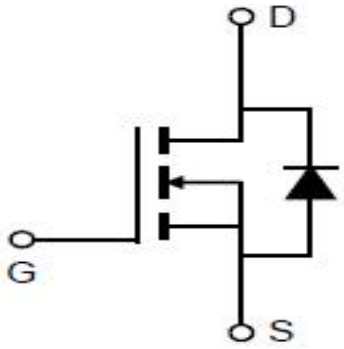
V_{DS}	100V
$R_{DS(on)typ.}$	1.5mΩ
VTH	3V
$I_{D（Silicon\ limit）}$	299A
$I_{D（Package\ limit）}$	240A
Ciss	12640pF
Qgd	59nC

Applications

- Power switching applications
- Power management for inverter systems
- Battery management

TO-247





Marking & Packing Information

Part #	Package	Marking	Tube/Reel	Qty(pcs)
DSC018N10N	TO-247	DSC018N10N	Tube	300/box

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	100	V
Gate-Source voltage	V_{GS}	±20	V
Continuous drain current T_C = 25°C （Silicon limit） T_C = 25°C （Package limit） T_C = 100°C	I_D	 299 240 189	A
Pulsed drain current (T_C = 25°C, t_p limited by T_{jmax})	$I_{D\ pulse}$	960	A
Avalanche energy, single pulse (L=0.5mH, Rg=25Ω)	E_{AS}	2352	mJ
Power dissipation T_C = 25°C	P_{tot}	313	W
Power dissipation T_A = 25°C	P_{tot}	2.0	W
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	°C

Notes:1.EAS was tested at Tj = 25℃, L = 0.5mH, Id=68A.

Thermal Resistance

Parameter	Symbol	Max	Unit
Thermal resistance, junction – case.	R_{thJC}	0.4	°C/W
Thermal resistance, junction – ambient(min. footprint)	R_{thJA}	62	

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Static Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Drain-source breakdown voltage	BV_{DSS}	100	-	-	V	V_{GS}=0V, I_D=250uA
Gate threshold voltage	$V_{GS(th)}$	2.0	3.0	4.0	V	V_{DS}=V_{GS},I_D=250uA
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	V_{DS}=100V,V_{GS}=0V T_j=25°C
		-	-	100		T_j=125°C
Gate-source leakage current	I_{GSS}	-	-	±100	nA	V_{GS}=±20V,V_{DS}=0V
Drain-source on-state resistance	$R_{DS(on)}$	-	1.5	1.8	mΩ	V_{GS}=10V, I_D=90A, Tj=25°C
Transconductance	g_{fs}	-	330	-	S	V_{DS}=5V,I_D=150A

Dynamic Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Input Capacitance	C_{iss}	-	12640	-	pF	V_{GS}=0V, V_{DS}=50V, f=1MHz
Output Capacitance	C_{oss}	-	2730	-		
Reverse Transfer Capacitance	C_{rss}	-	120	-		
Gate Total Charge	Q_G	-	212	-	nC	V_{GS}=10V, V_{DS}=50V, I_D=90A
Gate-Source charge	Q_{gs}	-	59	-		
Gate-Drain charge	Q_{gd}	-	59	-		
Gate plateau voltage	$V_{plateau}$	-	4.8	-	V	
Turn-on delay time	$t_{d(on)}$	-	43	-	ns	V_{GS}=10V, V_{DD}=50V, R_{G_ext}=3Ω, I_D=90A
Rise time	t_r	-	105	-		
Turn-off delay time	$t_{d(off)}$	-	117	-		
Fall time	t_f	-	159	-		

Body Diode Characteristic [1)]

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Diode Max Current	I_S		-	240	A	-
Diode Forward Voltage	V_{SD}	-	-	1.2	V	V_{GS}=0V,I_{SD}=90A
Diode Reverse Recovery Time	t_{rr}	-	116	-	ns	I_F=50A, dI/dt=100A/μs
Diode Reverse Recovery Charge	Q_{rr}	-	304	-	nC	

[1)] Defined by design. Not subject to full production test.

Typical Characteristics Diagram

Fig1. Output Characteristics

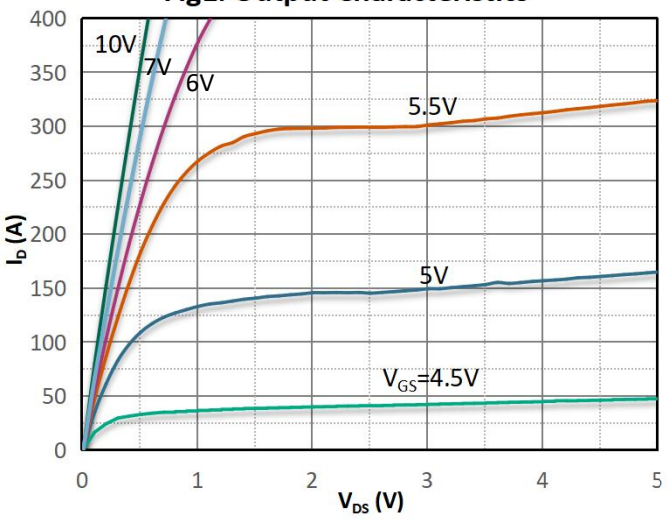


Fig2. Transfer Characteristics

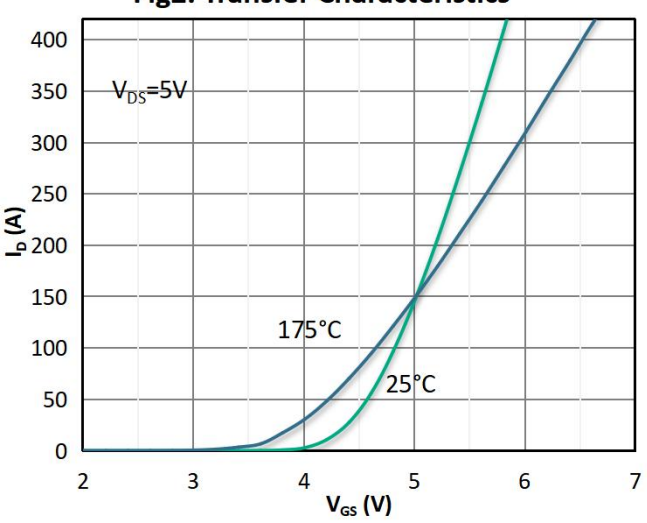


Fig3. Rds(on) vs Drain Current

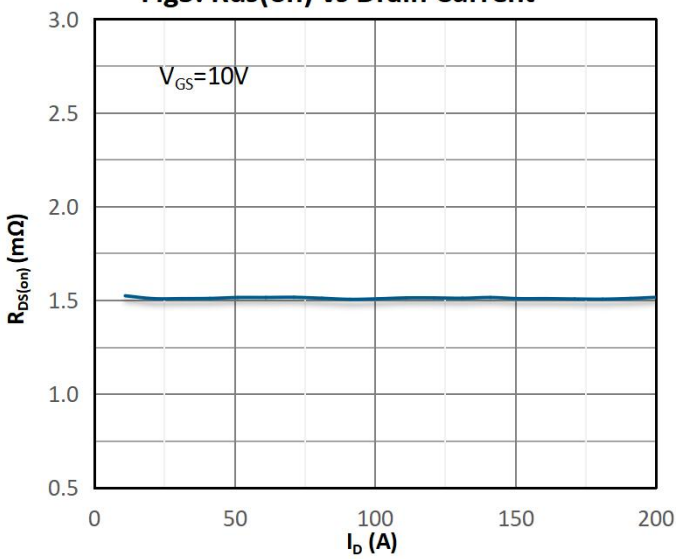


Fig 4. Rds(on) vs Gate Voltage

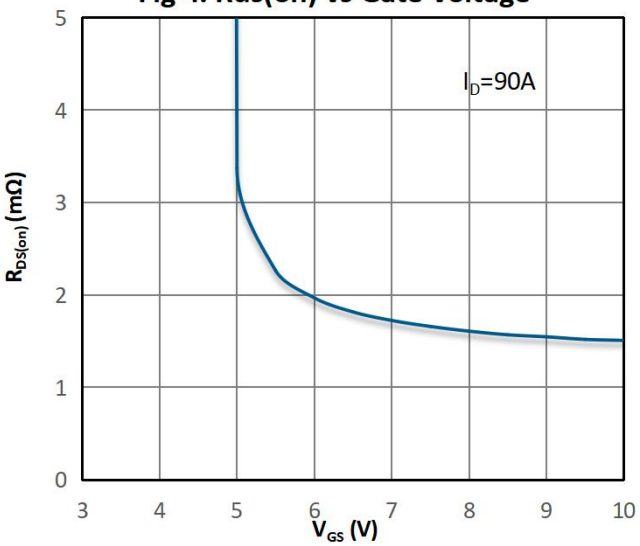


Fig5. Rds(on) vs. Temperature

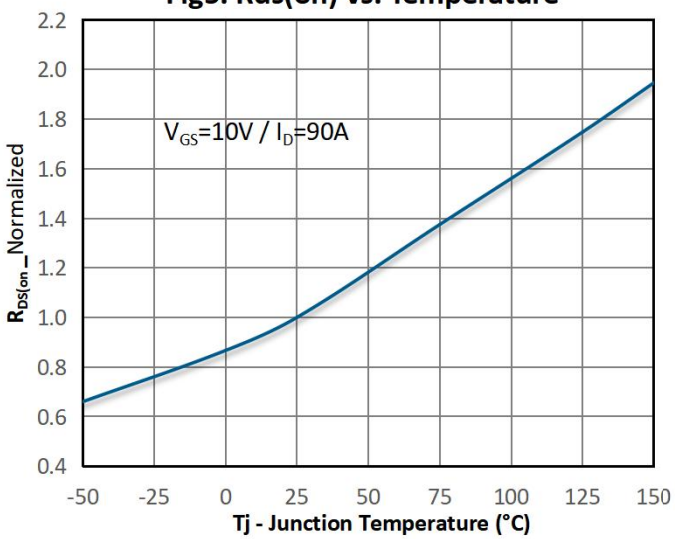
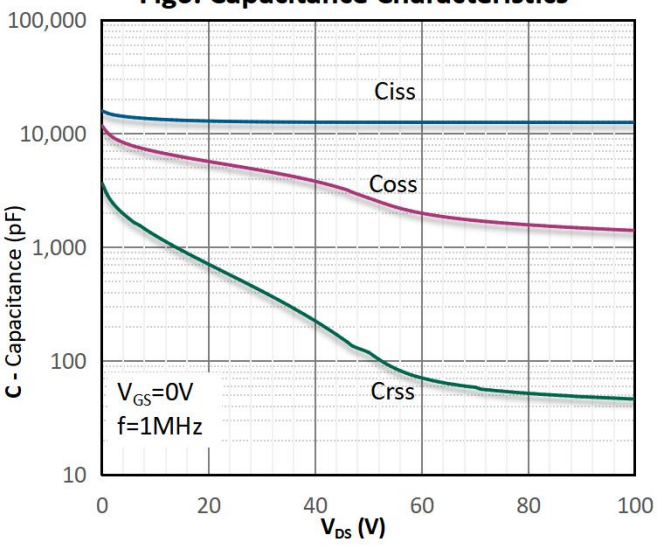


Fig6. Capacitance Characteristics



Typical Characteristics Diagram

Fig7. Gate Charge Characteristics

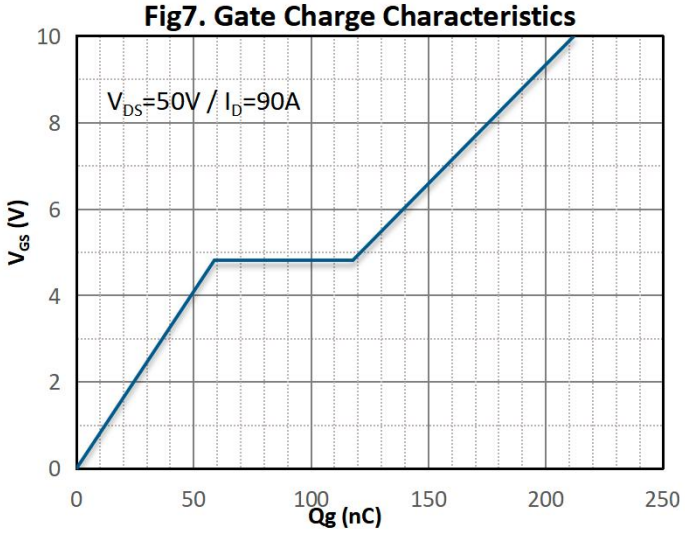


Fig8. Body-diode Forward Characteristics

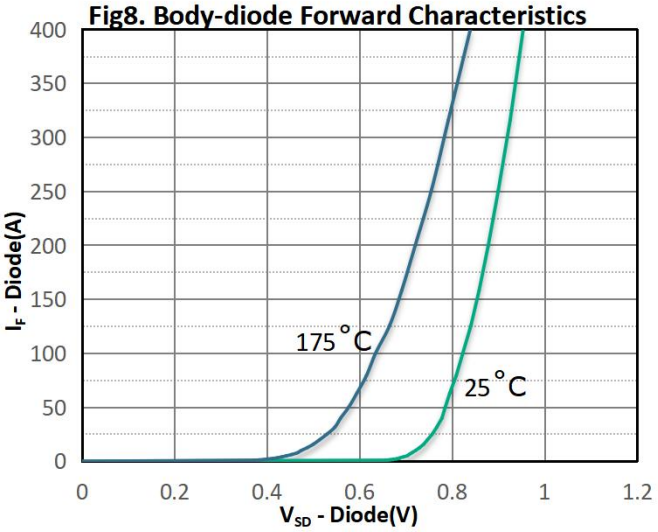


Fig9. Power De-rating

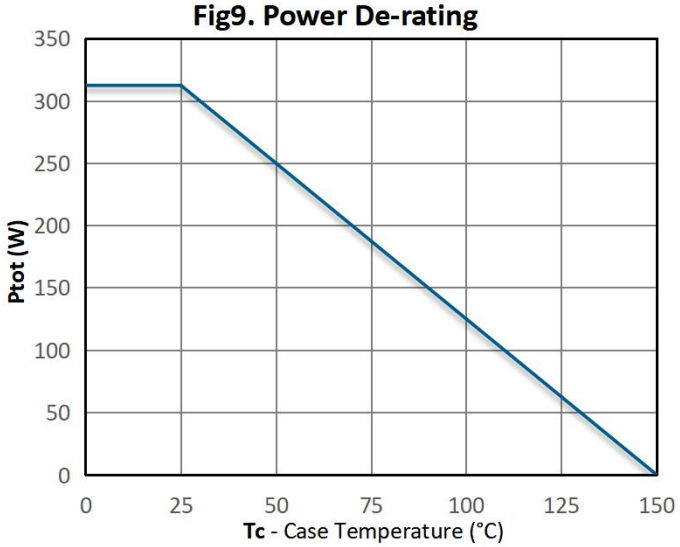


Fig10. Current De-rating

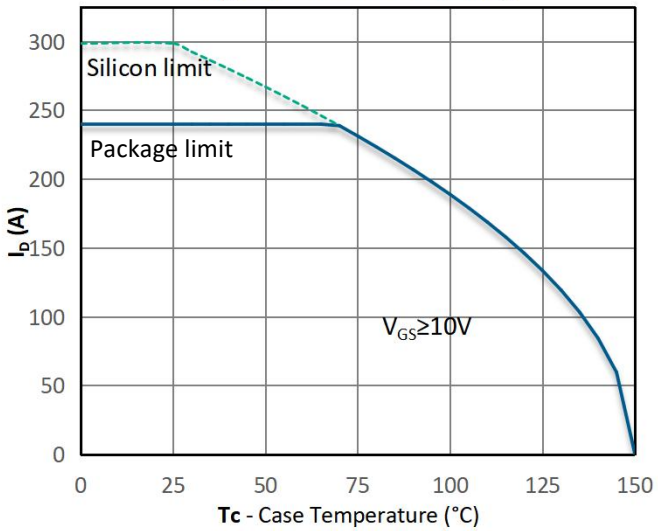


Fig11. Safe Operating Area

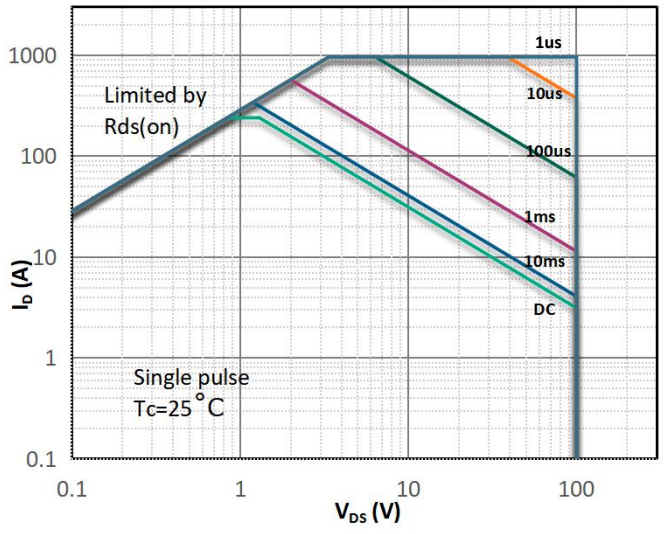
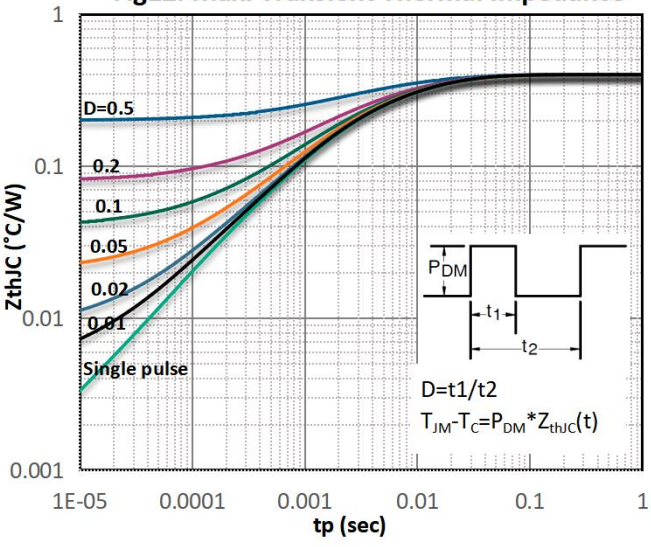
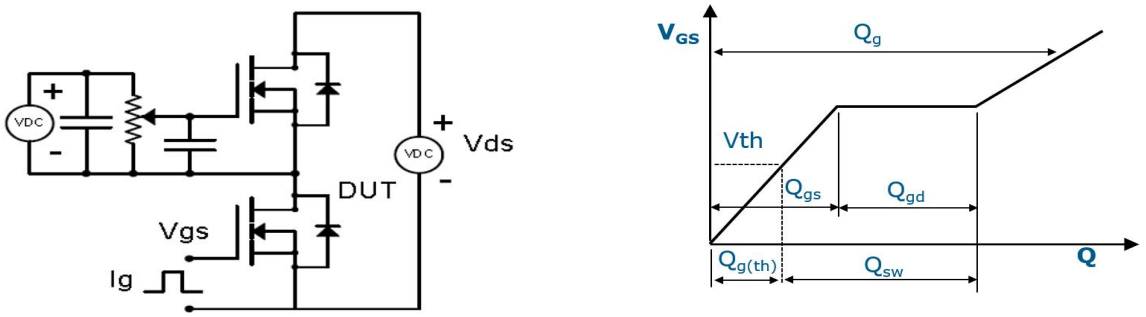


Fig12. Max. Transient Thermal Impedance

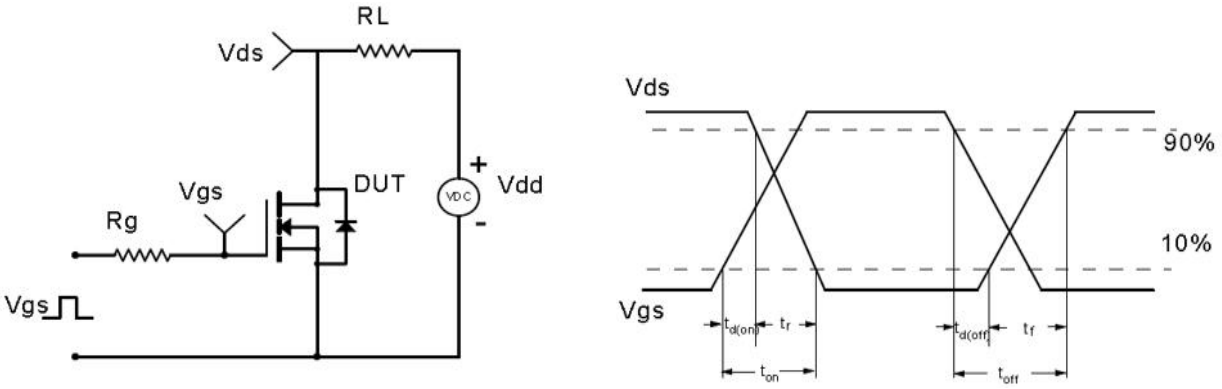


Test Circuit & Waveform

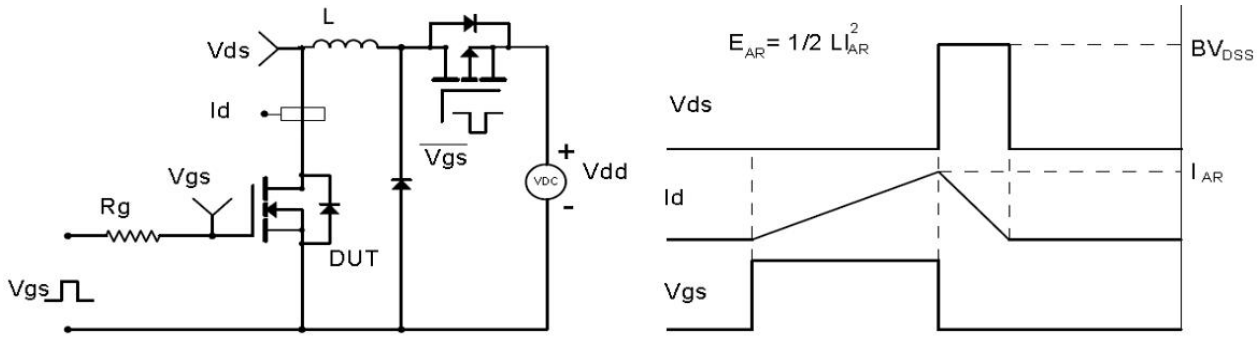
Gate Charge Test Circuit & Waveform



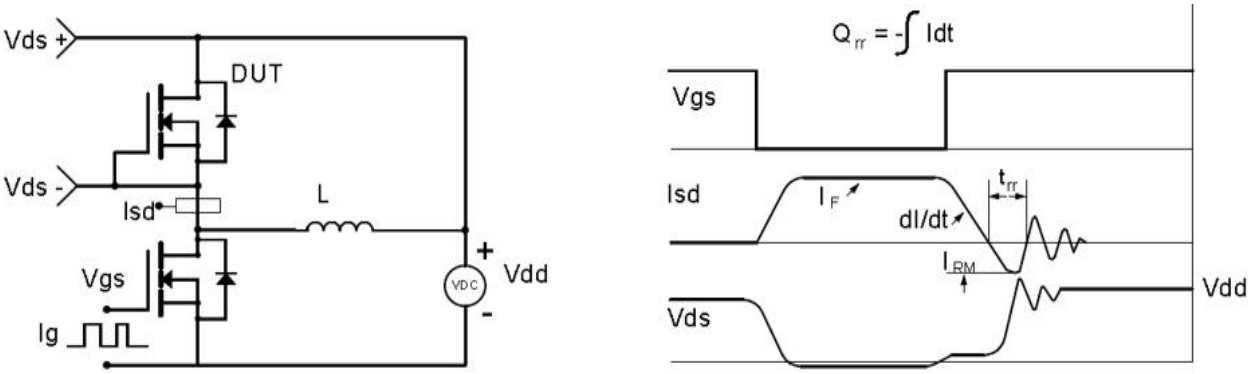
MOSFET Switching Test Circuit & Waveform



E_{AS} Test Circuit & Waveform

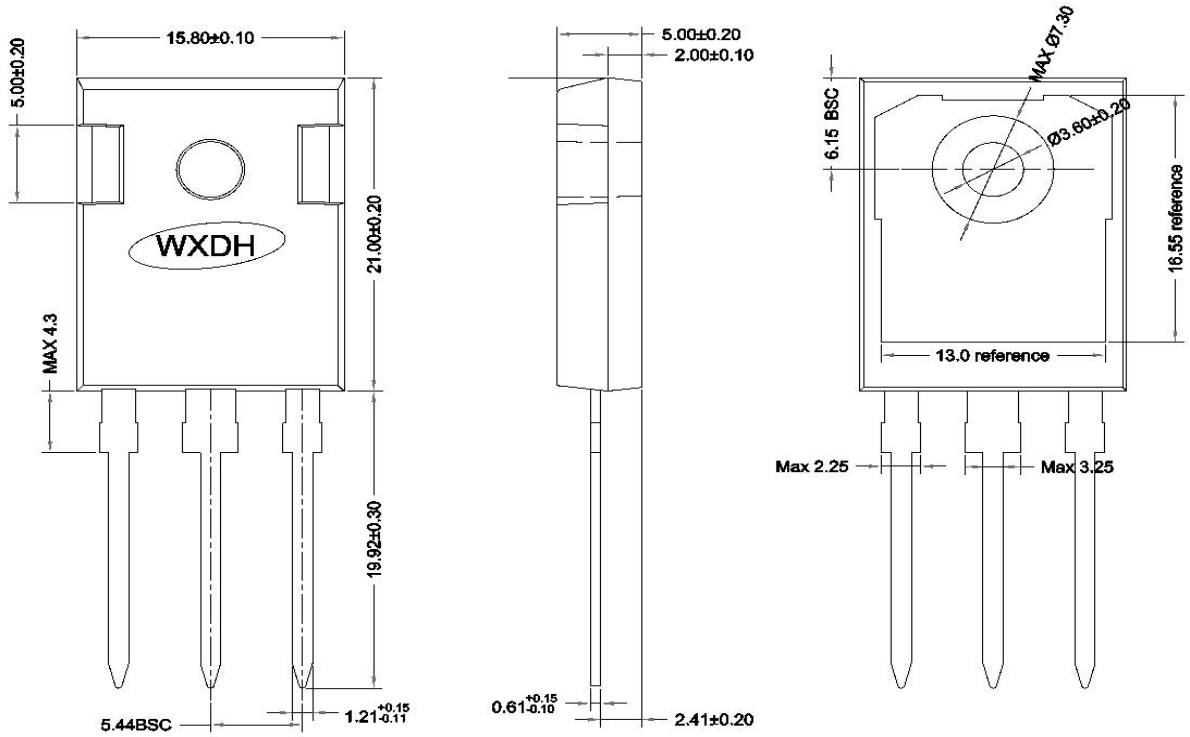


Diode Recovery Test Circuit & Waveform



Package Outline : TO-247

*Dimensions in mm



Revision History

Revison	Date	Major changes
1.0	2024/10/27	Release of formal version

Disclaimer

Data provided herein are measured under specified conditions; It is the customer's responsibility to evaluate the suitability of the product for the intended application.

Unless otherwise specified in the datasheet, the product is designed and qulified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as aviation, aerospace, life-support devices or systems.

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